

ABSTRACT OF THE DISCLOSURE

A thin film magnetic memory device includes: a TMR element, provided on a main surface of a silicon substrate, operating as a memory element; a buffer layer having a first surface bringing into contact with the
5 TMR element and a second surface, located on the side opposite to the first surface, having an area smaller than that of the first surface; and a bit line, formed of a conductor film and a barrier metal film that bring into contact with the second surface, extending in one direction so as to intersect the
10 TMR element. Thereby, it is possible to provide a thin film magnetic memory device realizing miniaturization of the memory cell and, also, having a high reliability, and a manufacturing method therefor.